

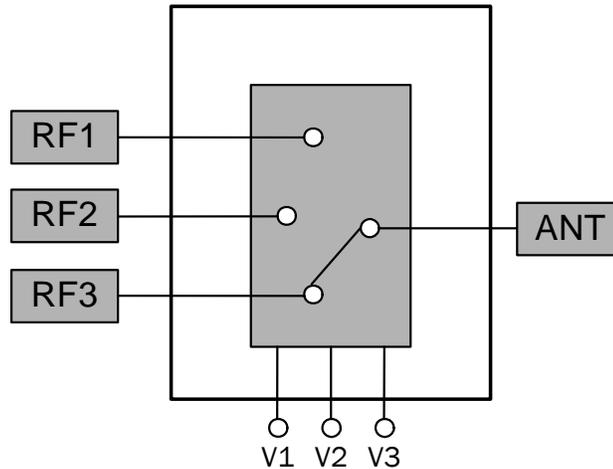


Features

- Broadband Performance
Low Frequency - 2.5GHz
- Low Insertion Loss
0.48dB Typ at 0.90GHz
0.68dB Typ at 1.90GHz
- Good Isolation:
23dB Typ at 1.90GHz
- Excellent Cross-Modulation Performance:
-102dBm Typ @ 0.90GHz
-100dBm Typ @ 1.90GHz
- PO.1dB > 34dBm
- Compact Footprint
(2.0mmx2.0mmx0.55mm,
12-pin QFN)

Applications

- CDMA Handset Applications
- Antenna Tuning Applications
- IEEE802.11b/g WLAN Applications
- Multi-mode GSM/W-CDMA Applications
- GSM/GPRS/EDGE Switch Applications



Functional Block Diagram

Product Description

The RF1132 is a single-pole triple-throw (SP3T) switch designed for CDMA Handset Applications and general purpose switching applications which require very low insertion loss and high power handling capability. The RF1132 is ideally suited for battery operated applications requiring high performance switching with very low DC power consumption. The RF1132 features low insertion loss, excellent cross-modulation performance, and good isolation. It is fabricated with 0.5µm GaAs pHEMT process, and is packaged in a very compact 2mmx2mm, 12-pin, leadless QFN package.

Ordering Information

RF1132 Broadband High Power SP3T Switch
RF1132PCBA-410 Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

- | | | | |
|--------------------------------------|--------------------------------------|------------------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

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Absolute Maximum Ratings

| Parameter | Rating | Unit |
|-------------------------------------------------------|-------------|------|
| Voltage | 6.0 | V |
| Maximum Input Power (0.6GHz to 2.5GHz), RF1, RF2, RF3 | +36 | dBm |
| Operating Temperature | -30 to +85 | °C |
| Storage Temperature | -65 to +100 | °C |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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| Parameter | Specification | | | Unit | Condition |
|---------------------------------|---------------|------|-------|------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| | Min. | Typ. | Max. | | |
| | | | | | $V_{CONTROL} = 0/2.6V$, Nominal Test Conditions Unless Otherwise Specified: $Z_0 = 50\Omega$. Temp = 25 °C. Need external DC blocking capacitors on all RF ports. |
| Operating Frequency | 0.6 | | 2.5 | GHz | |
| Insertion Loss | | | | | |
| Cellular | | 0.48 | 0.58 | dB | ANT to RFx ON, 824 MHz to 894 MHz |
| GPS | | 0.60 | 0.70 | dB | ANT to RFx ON, 1574 MHz to 1577 MHz |
| PCS | | 0.68 | 0.78 | dB | ANT to RFx ON, 1850 MHz to 1990 MHz |
| RF>ANT Isolation | | | | | |
| Cellular | 28 | 30 | | dB | RFxOFF to RFx ON, 824 MHz to 894 MHz |
| GPS | 23 | 25 | | dB | RFxOFF to RFx ON, 1574 MHz to 1577 MHz |
| PCS | 21 | 23 | | dB | RFxOFF to RFx ON, 1850 MHz to 1990 MHz |
| Second Harmonics | | | | | |
| Cellular | | -82 | -78 | dBc | +26 dBm input |
| PCS | | -84 | -80 | dBc | +26 dBm input |
| Third Harmonics | | | | | |
| Cellular | | -91 | -80 | dBc | +26 dBm input |
| PCS | | -95 | -82.5 | dBc | +26 dBm input |
| IIP3 | | | | | |
| IIP3 - Cellular (IMT, PCS, AWS) | 64 | 65 | | dBm | Two tones: +23 dBm, 837 MHz and 838 MHz |
| | | 67 | | dBm | Two tones: +23 dBm, 837 MHz and 838 MHz, $V_{CONTROL} = 3V$ |
| IIP3 - PCS | 61 | 63 | | dBm | Two tones: +23 dBm, 1880 MHz and 1881 MHz |
| | | 65 | | dBm | Two tones: +23 dBm, 1880 MHz and 1881 MHz, $V_{CONTROL} = 3V$ |
| Cross-Modulation | | | | | |
| Cellular | | -102 | -101 | dBm | PTx1 = 23 dBm @ 836 MHz, PTx2 = 23 dBm @ 837 MHz; $P_{INT} = -23$ dBm @ 881.5 MHz |
| | | -105 | | dBm | PTx1 = 23 dBm @ 836 MHz, PTx2 = 23 dBm @ 837 MHz; $P_{INT} = -23$ dBm @ 881.5 MHz, $V_{CONTROL} = 3V$ |
| PCS | | -100 | -96 | dBm | PTx1 = 23 dBm @ 1879.5 MHz, PTx2 = 23 dBm @ 1880.5 MHz; $P_{INT} = -23$ dBm @ 1960 MHz |
| | | -102 | | dBm | PTx1 = 23 dBm @ 1879.5 MHz, PTx2 = 23 dBm @ 1880.5 MHz; $P_{INT} = -23$ dBm @ 1960 MHz, $V_{CONTROL} = 3V$ |

| Parameter | Specification | | | Unit | Condition |
|-----------------------------------------------|---------------|------|------|------|----------------------------------------------|
| | Min. | Typ. | Max. | | |
| RF Port Return Loss | | | | | |
| RF>ANT | | -24 | -15 | dB | 0.5GHz to 2.0GHz |
| Input Power at 0.1dB Compression Point | | | | | |
| Cellular | | >+35 | | dBm | |
| PCS | | >+35 | | dBm | |
| Switching Speed | | | | | |
| T _{RISE} , T _{FALL} | | 0.80 | 1 | us | 10% to 90% RF, 90% to 10% RF |
| T _{ON} , T _{OFF} | | 0.80 | 1 | μs | 50% control to 90% RF, 50% control to 90% RF |
| DC Controls | | | | | |
| V _{HIGH} (V1, V2, V3) | | 2.6 | 3.6 | V | |
| V _{LOW} (V1, V2, V3) | 0 | | 0.4 | V | |
| Control Current | | 10 | | μA | |
| Leakage Current | | 10 | | μA | |

Switch Control Settings

| V1 | V2 | V3 | ANT-RF1 | ANT-RF2 | ANT-RF3 |
|----|----|----|---------|---------|---------|
| 1 | 0 | 0 | ON | OFF | OFF |
| 0 | 1 | 0 | OFF | ON | OFF |
| 0 | 0 | 1 | OFF | OFF | ON |

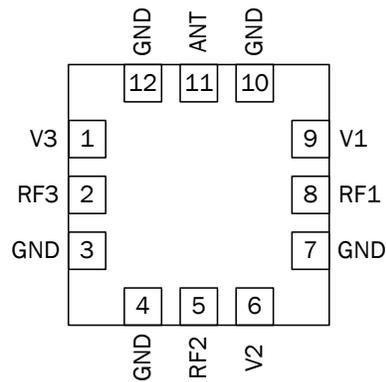
0: Logic level low, 0V to 0.4V

1: Logic level high, 2.6V to 3.6V

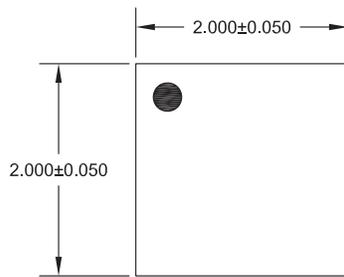
Note: Indeterminate states would lead to degraded performance.

| Pin | Function | Description |
|-----------------|------------|------------------------------------------------------------------------------------------------------------------------------------|
| 1 | V3 | Control Signal 3 |
| 2 | RF3 | RF Port 3 |
| 3 | GND | Ground |
| 4 | GND | Ground |
| 5 | RF2 | RF Port 2 |
| 6 | V2 | Control Signal 2 |
| 7 | GND | Ground |
| 8 | RF1 | RF Port 1 |
| 9 | V1 | Control Signal 1. |
| 10 | GND | Ground |
| 11 | ANT | Antenna Connection |
| 12 | GND | Ground |
| Pkg Base | N/C | Should be left floating for best performance. RF performance specifications in this DS are quoted with package base left floating. |

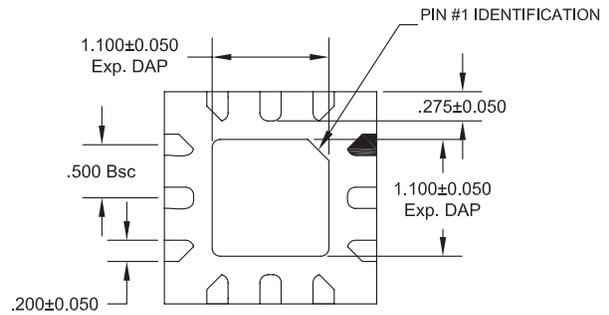
Pin Out



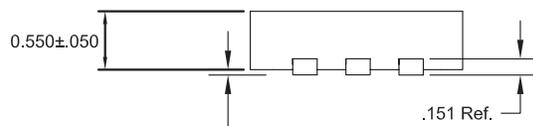
Package Drawing



TOP VIEW



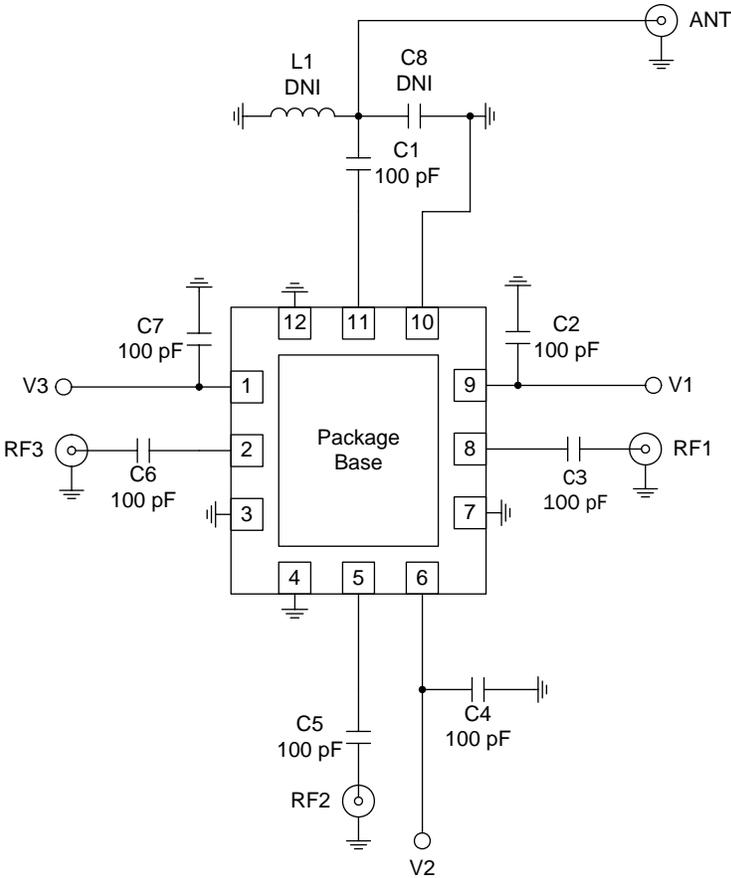
BOTTOM VIEW



SIDE VIEW

Notes:
1) Pin 1 Shaded Area

Evaluation Board Schematic



Note: Package Base needs to be left floating for best Isolation performance.

Typical Performance

